

SOT-23 Plastic-Encapsulate Transistors

SS8550 TRANSISTOR (PNP)

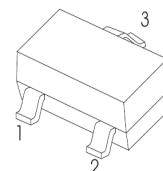
FEATURES

- High Collector Current
- Complementary to SS8050

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-1.5	A
P _C	Collector Power Dissipation	300	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	417	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

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1. BASE
2. EMITTER
3. COLLECTOR

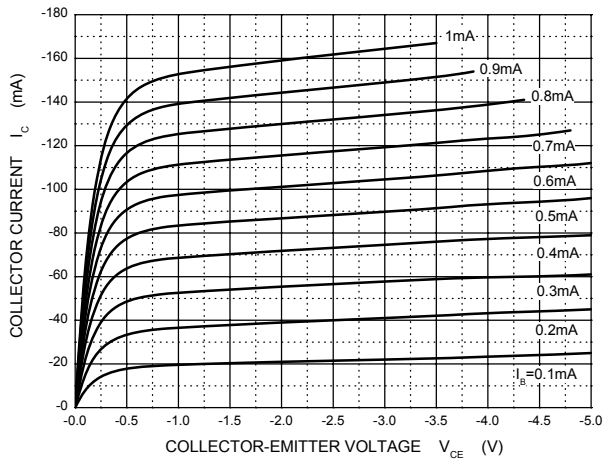
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-0.1mA, I _B =0	-25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0			-100	nA
Collector cut-off current	I _{CEO}	V _{CE} =-20V, I _B =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-100mA	120		400	
	h _{FE(2)}	V _{CE} =-1V, I _C =-800mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-800mA, I _B =-80mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-800mA, I _B =-80mA			-1.2	V
Base-emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-10mA			-1	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-50mA, f=30MHz	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			20	pF

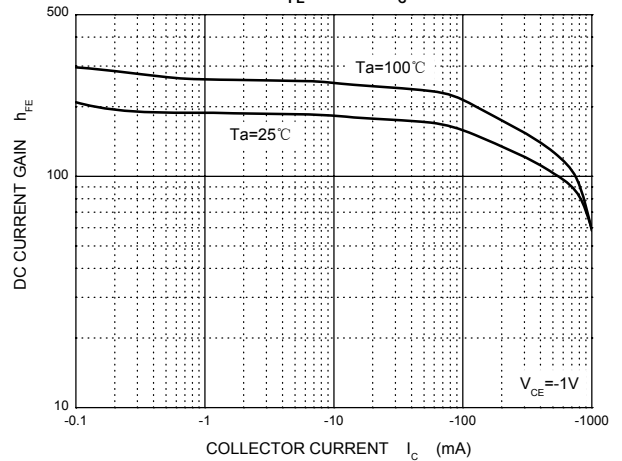
CLASSIFICATION OF h_{FE(1)}

RANK	L	H	J
RANGE	120 - 200	200 - 350	300 - 400
MARKING	Y2		

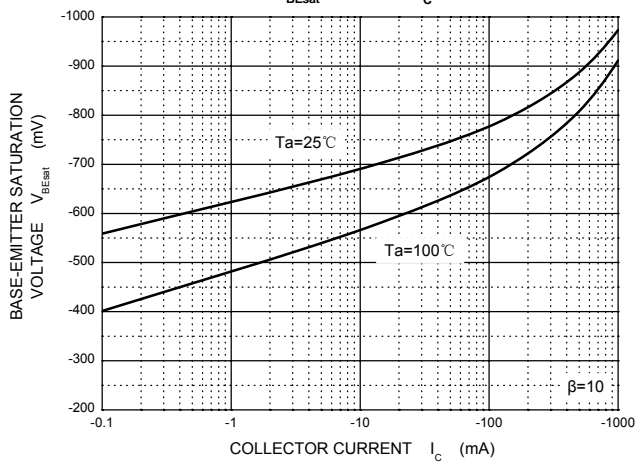
Static Characteristic



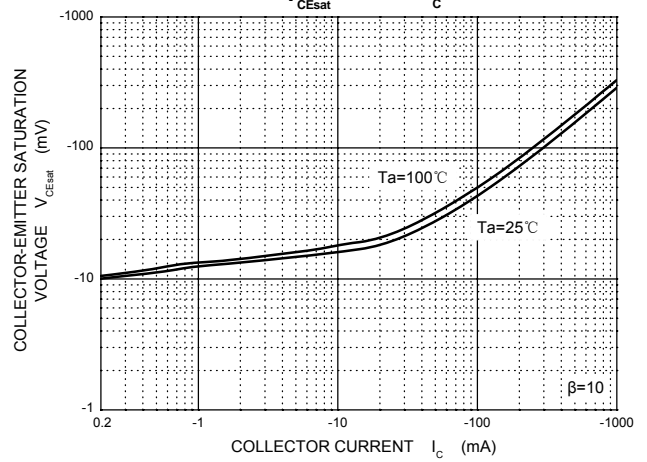
h_{FE} — I_c



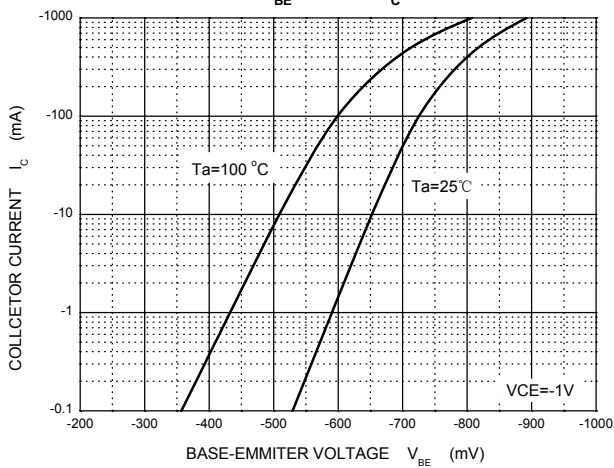
V_{BEsat} — I_c



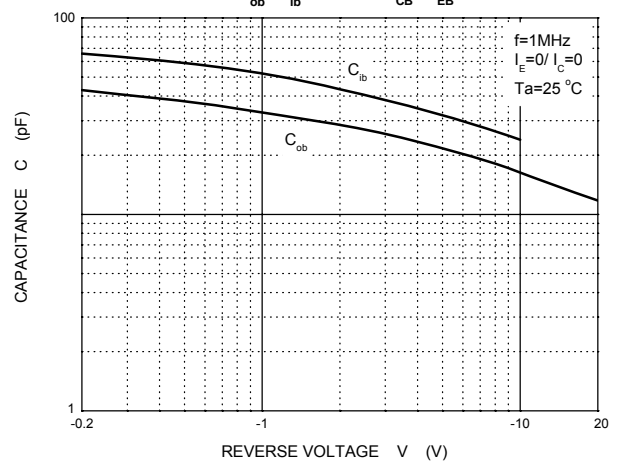
V_{CEsat} — I_c



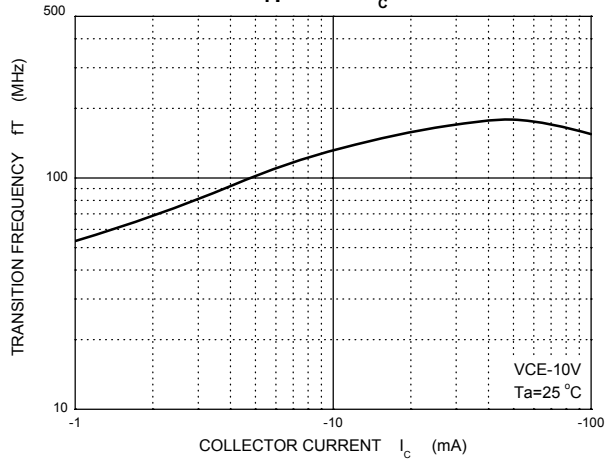
V_{BE} — I_c



C_{ob}/C_{ib} — V_{CB}/V_{EB}



f_T — I_c



P_c — T_a

